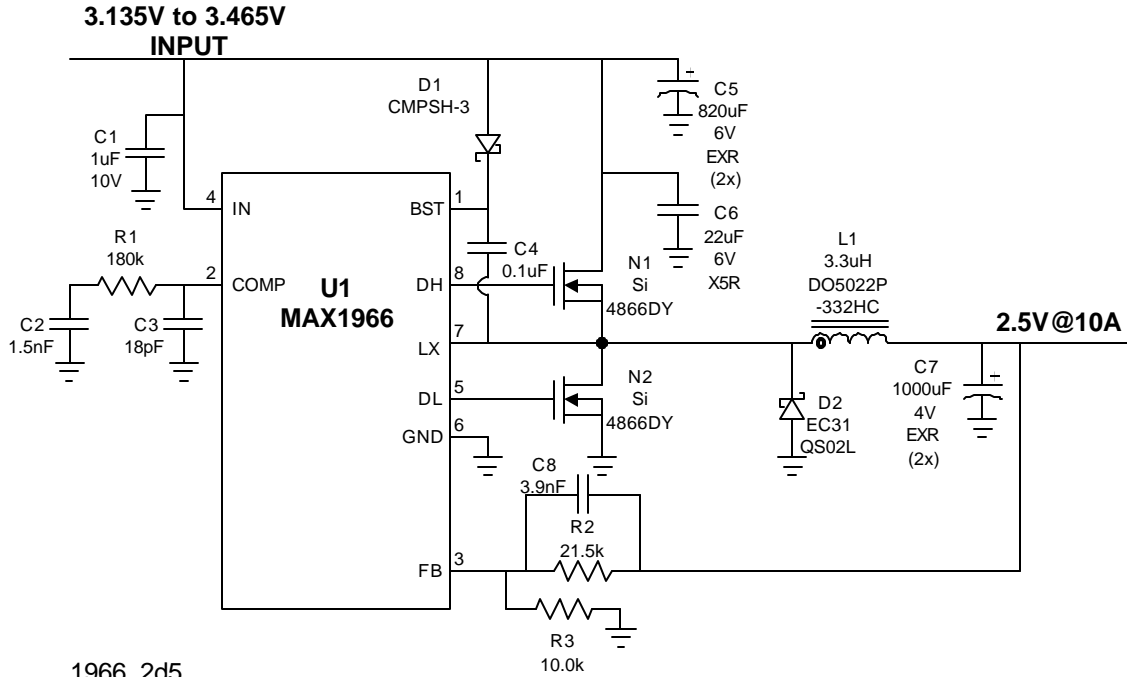


DDR RAM VDDQ Supply



V _{in}	I _{in}	V _{out}	I _{out}	Efficiency
3.3037	0.027	2.5208	0	
3.1030	8.833	2.5477	10.020	0.931
3.3027	8.336	2.5567	10.020	0.930
3.5023	7.892	2.5642	10.020	0.929
		50mV _{pp}		

BILL OF MATERIALS
3.135V to 3.465V Input
2.5V @ 10A Output
4/18/02

1966_2d5

DESIGNATION	QTY	DESCRIPTION
C1	1	1uF 10V X7R ceramic capacitor (0805) Taiyo Yuden LMK212BJ105MG
C2	1	1.5nF ceramic capacitor (0805)
C3	1	18pF ceramic capacitor (0805)
C4	1	0.1uF ceramic capacitor (0805)
C5	2	820uF 6V aluminum electrolytic capacitor Sanyo 6MV820EXR
C6	1	22uF 6V X5R ceramic capacitor (1210) Taiyo Yuden JMK325BJ226MM
C7	2	1000uF 4V aluminum electrolytic capacitor Sanyo 4MV1000EXR
C8	1	3.9nF ceramic capacitor (0805)
D1	1	100mA 30V Schottky diode (SOT-23) Central Semi CMPSH-3
D2	1	3A 20V Schottky diode Nihon EC31QS02L
L1	1	3.3uH Power inductor Coilcraft DO5022P-332HC
N1,N2	2	8.5m Ohm N-channel MOSFET (SO-8) Siliconix Si4866DY
R1	1	180k Ohm 5% resistor (0805)
R2	1	21.5k Ohm 1% resistor (0805)
R3	1	10.0k Ohm 1% resistor (0805)
U1	1	MAX1966EUB (10-uMAX)